Influence of AlO$_x$ Interlayers on LeTID Kinetics in Ga-Doped Cz-Si

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Abstract. Light and elevated temperature-induced degradation (LeTID) is causing efficiency drops especially in p-type silicon based solar cells. It is assumed to be strongly influenced by the hydrogen content in the bulk material. The presented work focuses on the impact of differently thick (5-25 nm) atomic layer-deposited aluminum oxide (AlO$_x$) interlayers underneath the hydrogen-rich silicon nitride (SiN$_y$:H) capping layer. The interlayer acts as a diffusion barrier for H during the firing step. It is demonstrated that the AlO$_x$ interlayer has a comparable effect on the LeTID kinetics in Ga-doped Cz-Si (Cz-Si:Ga) as it is observed in B-doped Cz-Si (Cz-Si:B). Additionally, it substantially minimizes lifetime degradation in the Cz-Si:Ga sample. With determined ratio of electron to hole capture cross sections $k=26(3)$, the degradation phenomena are attributed to the LeTID kinetics. Deposition of AlO$_x$ barrier layers exceeding 10 nm in thickness does not yield additional positive effects. Resistivity measurements revealed that the change in hole concentration correlates with the defect density for varying AlO$_x$ layer thicknesses. The doping concentration seems to influence the change in maximum defect density for varying AlO$_x$ layer thicknesses.

Keywords: Crystalline silicon, Surface passivation, Bulk defects, Degradation, Hydrogen

Introduction

Light and elevated temperature-induced degradation (LeTID) is known to have a significant impact on the efficiency of crystalline silicon (c-Si) solar cells due to a decrease in the charge carrier lifetime [1]. This may be followed by a phase of regeneration [2]. It is very likely that H is a key factor responsible for LeTID in B-doped silicon and it has already been shown that the amount of H in the c-Si bulk can be reduced by an AlO$_x$ layer beneath the SiN$_y$:H capping layer [3], [4]. This could be explained by the AlO$_x$ interlayer acting as a H diffusion barrier, which reduces the amount of H that diffuses into the c-Si during the firing step [5].

Ga-doped silicon does not suffer from BO-related degradation in B-doped c-Si but may suffer from LeTID, so it is very interesting to check its behavior concerning LeTID, as it is easier to be studied separately in this material. In this work, the influence of an AlO$_x$ interlayer on the degradation of the effective excess charge carrier lifetime $\tau_{\text{eff}}$ in Czochralski (Cz)-grown c-Si (Cz-Si:Ga) is investigated by comparison with Cz-Si:B material. To gain more insights about the H content in the c-Si bulk, GaH- and BH-pairs are determined via resistivity measurements.
Experimental

Ga- (0.7 \(\Omega\) cm and 1.8 \(\Omega\) cm) and B-doped (2.0 \(\Omega\) cm) Cz-Si material, laser cut to a size of 5x5 cm\(^2\), is used for \(\tau_{\text{eff}}\) measurements. After removal of the saw damage and a cleaning process, atomic layer deposition (ALD) is used to form AlO\(_x\) layers ranging between 5-25 nm in thickness at a deposition temperature of 300°C. Additionally, a reference sample group for each dopant is processed without an AlO\(_x\) barrier layer. All symmetrically processed samples received a SiN\(_y\):H layer on both sides with a thickness of 75 nm using plasma-enhanced chemical vapor deposition (PECVD). All samples are fired at a measured peak sample temperature of 800°C.

Lifetime analysis is carried out at 30°C by the photoconductance decay method after samples have been treated iso-generatively at 1.0(1) sun illumination and a temperature of 100°C for Ga- and B-doped samples. The measured \(\tau_{\text{eff}}\) is used to calculate the lifetime equivalent defect density \(\Delta N_{\text{eq}}\) for qualitative comparison of the different doping materials, as described in [6]. Photoconductive decay (PCD) measurements are used to determine \(\tau_{\text{eff}}\) evaluated at an excess charge carrier density of \(\Delta n = 0.1\ p_0\) with \(p_0\) being the dopant concentration. For the Ga-doped samples an additional evaluation of the saturation current density \(j_0\) is performed according to [7] and photoluminescence (PL) images are taken.

To determine the concentration of GaH- and BH-pairs by resistivity measurements [8], [9], Al is deposited in four lines on one side of the samples, followed by laser fired contacting (LFC). B- and Ga-doped samples for resistivity measurements have been annealed at 180°C in the dark. Once the measured resistivity of Ga-doped samples saturated, a further treatment at 300(1)°C and 2.0(2) suns is performed.

Results and discussion

Comparison of defect densities for Ga- and B-doped samples

The upcoming results should only be interpreted qualitatively since the doping concentration between B- and Ga-doped samples vary. Therefore, only the lifetime equivalent defect density (\(\Delta N_{\text{eq}}\)) will be compared to observe trends in the shown data.

The resulting \(\Delta N_{\text{eq}}\) of the Cz-Si:Ga material with varying AlO\(_x\) barrier thickness is shown in Fig. 1 (a). Without any barrier layer between the H-rich SiN\(_y\):H and the c-Si bulk, \(\Delta N_{\text{eq}}\) is increasing for the first few minutes of the treatment. After reaching the maximum \(\Delta N_{\text{eq}}\), regeneration can be observed. With the addition of the AlO\(_x\) interlayer beneath the SiN\(_y\):H with a thickness of 5-25 nm, the observed defect density is lowered. For better visibility, a fitting with three exponential functions is added to the data points. There is no further reduction of the defect density visible for an AlO\(_x\) interlayer with a thickness >10 nm. The capture cross-section ratio \(k\) for the defect after roughly one day of degradation is calculated to \(k = 26(3)\) which seems to be in good accordance with literature [10]. The time constants from the exponential fitting are determined as \(t_1=0.35(4)\ h\), \(t_2=15(4)\ h\), \(t_3=23(6)\ h\) and present a degradation with a following regeneration of the Ga-doped material. Starting lifetimes for these samples are between 300 \(\mu\)s and 600 \(\mu\)s.

The saturation current density is evaluated to monitor surface degradation. Fig. 1 (b) illustrates \(j_0\) for the Ga-doped samples subjected to 100°C, 1.0 sun. Samples with an AlO\(_x\) interlayer are evaluated using the standard slope-based method. In the case of the reference sample, this evaluation results in an underestimation of \(j_0\). To address this issue, a new difference analysis method is used [11]. All samples maintained a relatively constant \(j_0\) during degradation, indicating that the degradation of \(\tau_{\text{eff}}\) is a bulk related phenomenon mainly caused by
LetID kinetics as it is observable for \( \Delta N_{\text{leq}} \) in Fig. 1 (a). However, the sample without any interlayer exhibits an increase of \( j_0 \) after approximately 100 h pointing towards a degradation of surface passivation quality.

![Graph](image.png)

**Figure 1.** (a) \( \Delta N_{\text{leq}} \) over accumulated time during iso-generative degradation at 100°C, 1.0(1) sun in Cz-Si:Ga (0.7 \( \Omega \) cm) (b) Corresponding saturation current density \( j_0 \), with dashed lines as guide for the eyes, over the accumulated time at 1.0(1) sun at 100°C for the 0.7 \( \Omega \) cm Ga-doped samples.

Additionally, PL images for the degradation of the Ga-doped samples are shown in Fig. 2. The sample without AlO\(_x\) interlayer shows a significant degradation after 22.5 h (time of maximum degradation of the sample without AlO\(_x\) layer), which is consistent with the results obtained from \( \Delta N_{\text{leq}} \) measurements. In contrast, there is barely any degradation visible for the samples with AlO\(_x\) layer. Though, it should be noted that the injection is higher for the evaluation with PL compared to PCD with \( \Delta n = 0.1 \, \text{p}_0 \), resulting in less pronounced differences. This could be the reason no visible degradation is observed for the sample with a 5 nm AlO\(_x\) interlayer. All samples keep their homogeneity during the illuminated treatment.

![PL images](image.png)

**Figure 2.** PL images of the Cz-Si:Ga (0.7 \( \Omega \) cm) samples with various AlO\(_x\) interlayer thicknesses before degradation (top) and after 22.5 h of illumination at 1.0(1) sun and 100°C (bottom).

For a direct comparison, similarly doped Cz-Si:Ga (1.8 \( \Omega \) cm) and Cz-Si:B (2.0 \( \Omega \) cm) samples are processed and treated under the same conditions. Fig. 3 shows the defect density for Ga- and B-doped samples with varying AlO\(_x\) interlayer thicknesses over the accumulated time during treatment at 1.0(1) sun iso-generative illumination at 100(1)°C. The defect density \( \Delta N_{\text{leq}} \) for the B-doped samples is significantly higher (\( \Delta N_{\text{leq,max}} > 20 \, \text{ms}^{-1} \)) compared to the Ga-doped samples (\( \Delta N_{\text{leq,max}} < 3 \, \text{ms}^{-1} \)). With increasing thickness of the AlO\(_x\) interlayer, a decrease in the defect density is observed for both Ga- and B-doped samples, but the relative decrease is
more significant for the Ga-doped samples as it was already observed in Fig. 1 (a). The reference samples for each dopant without interlayer exhibit another increase in defect density after roughly 40 h of treatment, which can again be related to the degradation of surface passivation.

Figure 3. Direct comparison of defect densities $\Delta N_{eq}$ over accumulated time during iso-generative degradation at 1.0(1) sun for Cz-Si:B (2.0 $\Omega$cm) and Cz-Si:Ga (1.8 $\Omega$cm) with AlO$_x$ interlayers of 6 nm and 16 nm and a reference, respectively.

It is likely that the effect of the reduced H diffusion from the SiN$_x$:H layer into the c-Si bulk affects the LeTID kinetics in the Cz-Si:Ga similarly to the kinetics in Cz-Si:B. Further experiments, determining the concentration of GaH- and BH-pairs by resistivity measurements to gain more insights regarding the H content in the bulk, will be discussed in the next section.

**Determination of GaH- and BH-pairs via resistivity measurements**

The H content in Ga- and B-doped samples is investigated by the determination of GaH- and BH-pairs via resistivity measurements. This involves a process whereby H$_2$ dimers dissociate and form GaH- and BH-pairs with the corresponding dopant species, which results in a depletion of holes and thus increase in resistivity. Fig. 4 displays changes in hole concentration during dark anneal at 180(1)$^\circ$C (left) followed by illumination at 2.0(2) suns at 300(1)$^\circ$C (right) over the accumulated treatment time for Cz-Si:Ga (0.7 $\Omega$cm) considering different AlO$_x$ layer thicknesses. It can be observed that the maximum of the change in hole concentration saturates at around 2.5x10$^{14}$ cm$^{-3}$ for an AlO$_x$ interlayer exceeding 10 nm in thickness during. This observation aligns with the findings on defect densities presented in Fig. 1 (a).

Figure 4. Change in hole concentration $\Delta p$ over accumulated time during dark anneal at 180$^\circ$C (left) and illumination (2.0 suns, 300$^\circ$C) (right) for Cz-Si:Ga (0.7 $\Omega$cm) samples with varying AlO$_x$ layer thickness between 5-25 nm and a reference without interlayer.
Comparable samples to those presented in Fig. 3 underwent resistivity measurements to identify GaH-pairs in the 1.8 Ωcm Ga-doped material and BH-pairs in the 2 Ωcm B-doped material. The observed association and dissociation of GaH- (a) and BH- (b) pairs through changes in hole concentration over accumulated time across varying AlOx interlayer thicknesses is depicted in Fig. 5. For both types of dopants, a similar trend is observable but the maximum Δp is lower for B-doped samples. Comparing the resistivity measurements of the 0.7 Ωcm Ga-doped material in Fig. 4 with the 1.8 Ωcm doped material in Fig. 5 (a) indicates a different behavior for variations of the AlOx barrier thickness.

**Figure 5.** Change in hole concentration Δp over accumulated time for Cz-Si:Ga (1.8 Ωcm) during dark anneal at 180°C on the left and illumination at 300°C on the right (a) and Cz-Si:B during dark anneal at 180°C (b) for AlOx interlayers of 6 nm and 16 nm compared to a reference sample without interlayer.

Qualitative analysis of the influence of AlOx thickness on ΔN_{eq} and Δp

Finally, Fig. 6 summarizes the results on resistivity and lifetime equivalent defect densities by comparing the maximum defect densities ΔN_{eq,max} (left scale) with the maximum change in hole concentration Δp_{max} (right scale) depending on the thickness of applied AlOx interlayer for all materials used in this work.

**Figure 6.** Maximum defect densities (at 100°C, 1 sun) and maximum change in hole concentration for all samples fired at a measured peak temperature of 800°C in dependence of the AlOx interlayer thickness.

This representation enables a comparison between defect densities of differently doped Ga-doped and B-doped samples with their corresponding maximum GaH- and BH-pair association. In addition, the comparison is limited to samples that were specifically prepared for this
research in order to ensure consistency of preparation and measurement procedures across different materials. Note that all lifetime samples are treated under 1 sun illumination at 100°C, and therefore reaction equilibriums might change for different doping concentrations. Based on the data presented, it appears that defect densities are higher in B-doped samples compared to those doped with Ga. Additionally, it seems that the behavior of defect density and change in hole concentration with increasing AlOx thickness is influenced by the doping concentration which can be observed by the change in steepness for the two doping concentrations of Ga-doped samples. Notably, in the case of B-doped material, saturation of ΔN_{eq,max} is not observed until a layer thickness of 16 nm, which contrasts with the observed saturation in resistivity measurements for AlOx layers thicker than 6 nm.

The decline in ΔN_{eq,max} for increased barrier thicknesses is steeper than the decline in Δp_{max} for all samples. This aligns with previous findings that the amount of H is not the only factor influencing the defect density and that other mechanisms may become a dominant factor as the barrier thickness increases. Furthermore, a crossover between the 2 Ωcm B-doped material and the 0.7 Ωcm Ga-doped material around an interlayer thickness of 10 nm appears. For the 1.8 Ωcm Ga-doped material this cannot be observed. Surprisingly, the amount of GaH-pairs in the maximum associated state is almost the same for the two doping concentrations in Ga-doped samples. Another observation is that the saturation of Δp_{max} is only visible for layer thicknesses exceeding 15 nm for the 0.7 Ωcm Ga-doped samples. In case of the defect density, a saturation is visible for AlOx layers exceeding 10 nm in thickness. It should be noted that this research only considers a limited range of materials and interlayer thicknesses, which makes it difficult to draw general conclusions about how these parameters influence defect formation.

Conclusion

In conclusion, the present study shows the impact of AlOx barrier thickness on the defect densities and hydrogen content in Cz-Si:B and Cz-Si:Ga materials under LeTID conditions. Defect density and surface-related degradation are strongly reduced by implementation of an AlOx interlayer between the bulk material and the SiN$_x$:H for Cz-Si. Moreover, the Ga-doped samples (1.8 Ωcm) exhibit a lower defect density compared to B-doped samples under 1.0(1) sun at 100(1)°C which is in contrast to Δp_{max}. Determination of GaH- and BH-pairs by resistivity measurements reveal that the amount of H correlates with the observed ΔN_{eq} for B- and Ga-doped materials. The decline in maximum defect densities with increasing barrier thickness is steeper than the decline in maximum change in hole concentration. Saturation of maximum change in hole concentration is visible for 0.7 Ωcm Ga-doped samples with layer thicknesses >15 nm, while saturation of defect density is visible for AlOx layers >10 nm. Further investigations regarding the influence of various doping concentrations on H content and LeTID dynamics should be executed.

Data availability statement

The data that support the findings of this study are available from the corresponding author upon reasonable request.

Author contributions

J. Kamphues: formal analysis, investigation, validation, visualization, conceptualization, writing - original draft; A. Schmid: Investigation, formal analysis, software; R. Fischer-Süßlin: investigation; G. Hahn: funding acquisition, project administration, resources, supervision, writing – review & editing; F. Geml: project administration, conceptualization, supervision, writing – review & editing
Competing interests

The authors declare that they have no competing interests.

Funding

Part of this work was financially supported by the German Federal Ministry for Economic Affairs and Climate Action (FKZ 03EE1102C). The content is the responsibility of the authors.

Acknowledgement

The author would like to thank Jochen Simon for in-depth discussion about the formation of GaH pairs and Axel Herguth for insights about the evaluation of $j_0$.

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